

30V P-Channel Enhancement Mode MOSFET

Voltage -30 V

Current

-77 A

Features

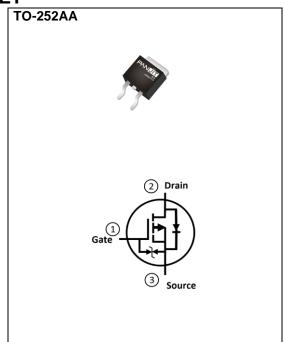
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-20A<8.4m\Omega$
- RDS(ON), VGS@-4.5V, ID@-10A<13.5m Ω
- 100% UIS tested
- Reliable and Rugged
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.3217 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-30	V	
Gate-Source Voltage		V_{GS}	±25	V	
Continuous Drain Current(Note 3)	T _C =25°C	l _D	-77		
	Tc=100°C		-54	Α	
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	-225		
Power Dissipation	T _C =25°C	Po	79	107	
	Tc=100°C		40	W	
Continuous Drain Current(Note 4)	T _A =25°C	l _D	-15	^	
	T _A =70°C		-12.5	A	
Power Dissipation	T _A =25°C	D-	3	W	
	T _A =70°C	Pb	2.1		
Single Pulse Avalanche Energy ^(Note 5)		Eas	100	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance ^(Note 4)	Junction to Case	R _{0JC}	1.9	°C/W	
	Junction to Ambient	$R_{\theta JA}$	50		



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA		-	-	.,	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.7	-2.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-20A	-	6.7	8.4	mΩ	
		V _{GS} =-4.5V, I _D =-10A	-	10.4	13.5		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	uA	
Gate-Source Leakage Current		V _{GS} =±25V, V _{DS} =0V	-	-	±10	uA	
	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	-	±1		
Dynamic (Note 6)							
Total Gate Charge	Qg	., ., ., ., .,	-	54	-	nC	
Gate-Source Charge	Qgs	V _{DS} =-24V, I _D =-20A,	-	6	-		
Gate-Drain Charge	Q _{gd}	V _{GS} =-10V	-	17	-		
Input Capacitance	Ciss), osy, v, ov,	-	2309	-	pF	
Output Capacitance	Coss	V _{DS} =-25V, V _{GS} =0V,	-	327	-		
Reverse Transfer Capacitance	Crss	f=1MHz	-	262	-		
Gate resistance	Rg	f=1MHz	-	2.3	-	Ω	
Turn-On Delay Time	td _(on)	., ., ., ., .,	-	11	-		
Turn-On Rise Time	t _r	V _{DS} =-24V, I _D =-20A,	-	9	-	ns	
Turn-Off Delay Time	td _(off)	V_{GS} =-10V, R_{G} =3 Ω	-	37	-		
Turn-Off Fall Time	tf	(11010 2)	-	21	-		
Drain-Source Diode							
Diode Forward Current	Is	T 05°0	-	-	-77	А	
Pulsed Diode Forward Current	I _{SM}	T _C =25°C	-	-	-225		
Diode Forward Voltage	V _{SD}	Is=-20A, V _{GS} =0V	-	-0.85	-1.3	V	
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =-20A	-	22	-	ns	
Reverse Recovery Charge	Qrr	dls/dt=100A/us	_	10	-	nC	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I_{AS} =-20A, V_{DD} =-30V, V_{GS} =-10V, Starting T_{J} =25°C.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

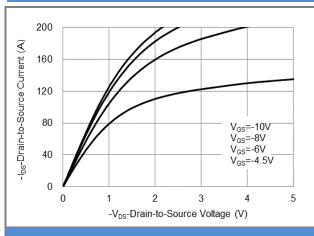


Fig.1 On-Region Characteristics

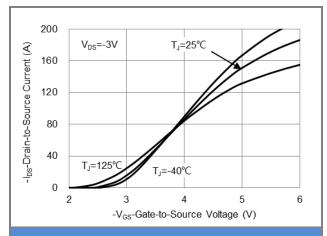


Fig.2 Transfer Characteristics

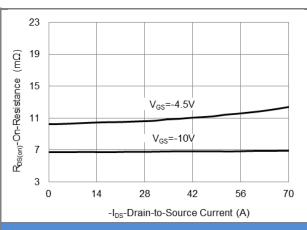


Fig.3 On-Resistance vs. Drain Current

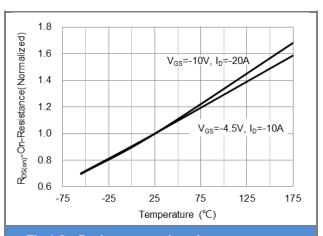


Fig.4 On-Resistance vs. Junction temperature

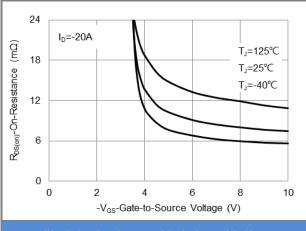


Fig.5 On-Resistance Variation with V_{GS}

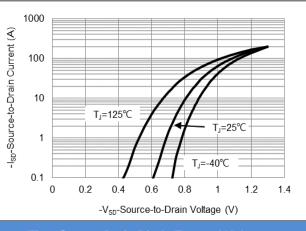


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

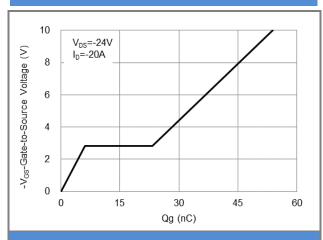


Fig.7 Gate-Charge Characteristics

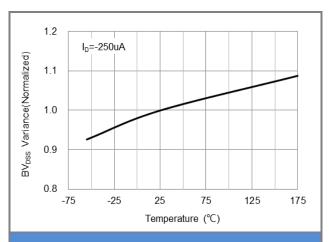


Fig.8 Breakdown Voltage Variation vs. Temperature

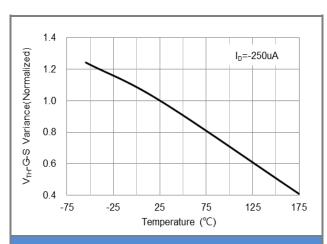


Fig.9 Threshold Voltage Variation with Temperature

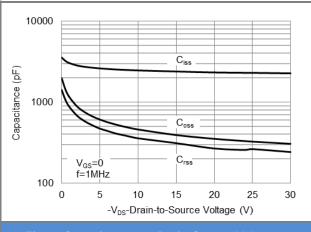
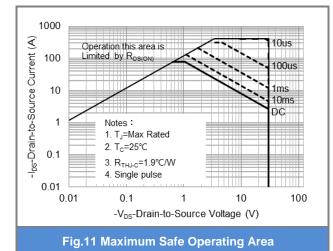


Fig.10 Capacitance vs. Drain-Source Voltage



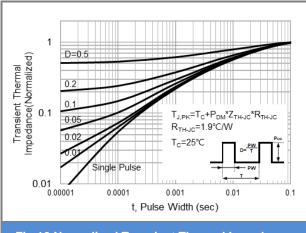


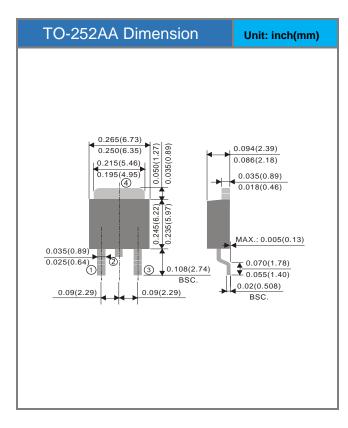
Fig.12 Normalized Transient Thermal Impedance

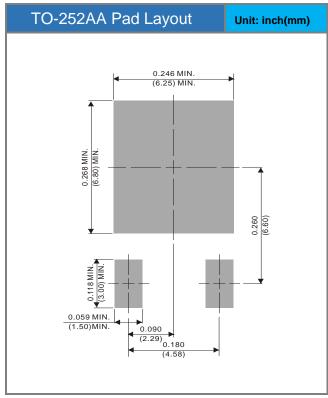


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJD70P03E-AU	TO-252AA	3K pcs / 13" reel	D70P03E	

Packaging Information & Mounting Pad Layout







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